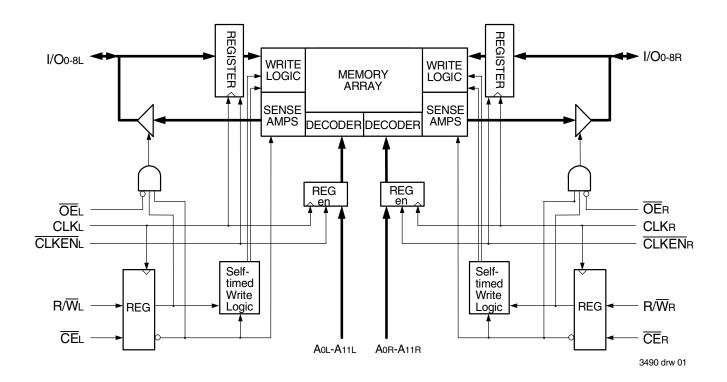
## HIGH SPEED 36K (4K X 9) SYNCHRONOUS DUAL-PORT RAM

### Features

- High-speed clock-to-data output times
  Commercial: 12ns (max.)
- Low-power operation
  - IDT70914S Active: 850 mW (typ.) Standby: 50 mW (typ.)
- Architecture based on Dual-Port RAM cells
  Allows full simultaneous access from both ports
- Clock Enable feature
- TTL-compatible, single 5V (± 10%) power supply

- Synchronous operation
  - 4ns setup to clock, 1ns hold on all control, data, and address inputs
  - Data input, address, and control registers
  - Fast 12ns clock to data out
  - Self-timed write allows fast cycle times
  - 16ns cycle times, 60MHz operation
- Guaranteed data output hold times
- Available in an 80-pin TQFP
- Green parts available, see ordering information

## Functional Block Diagram



DSC-3490/12

### High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

### Description

The IDT70914 is a high-speed 4K x 9 bit synchronous Dual-Port RAM. The memory array is based on Dual-Port memory cells to allow simultaneous access from both ports. Registers on control, data, and address inputs provide low set-up and hold times. The timing latitude provided by this approach allow systems to be designed with very short cycle times. With an input data register, this device has been optimized for applications having unidirectional data flow or bidirectional data flow in bursts.

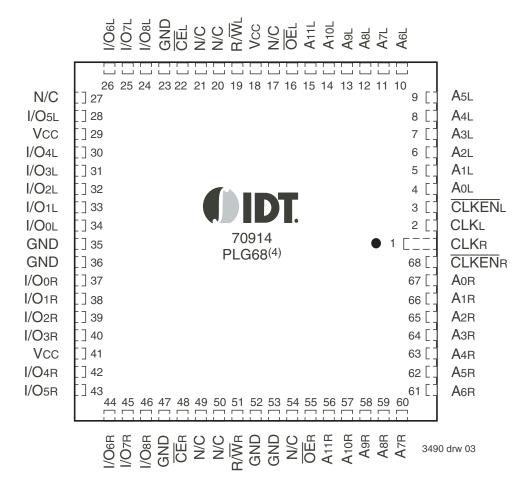
The IDT70914 utilizes a 9-bit wide data path to allow for parity at the

user's option. This feature is especially useful in data communication applications where it is necessary to use a parity bit for transmission/ reception error checking.

Fabricated using CMOS high-performance technology, these Dual-Ports typically operate on only 850mW of power at maximum high-speed clock-to-data output times as fast as 12ns. An automatic power down feature, controlled by  $\overline{CE}$ , permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT70914 is packaged in an 80-pin TQFP.

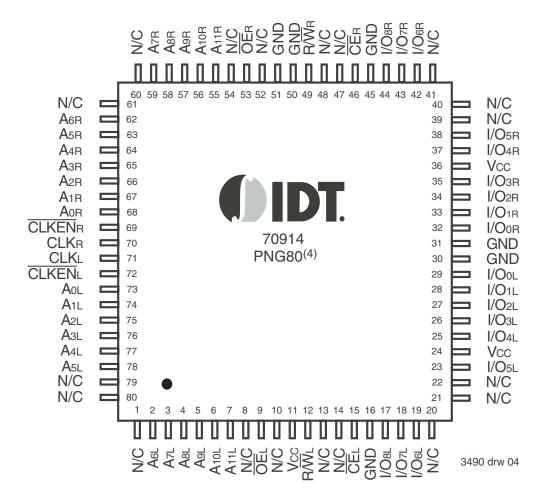
# Pin Configurations<sup>(1,2,3)</sup>



- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. J68-1 package body is approximately .95 in x .95 in x .17 in.
- 4. This package code is used to reference the package diagram.

70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

Pin Configuration<sup>(1,2,3)</sup> (con't.)



- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. PN80-1 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.

### High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

### Absolute Maximum Ratings<sup>(1)</sup>

	,	Unit
Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Terminal Voltage	-0.5 to Vcc	V
Temperature Under Bias	-55 to +125	٥C
stg Storage - Temperature -		٥C
DC Output Current	50	mA
	with Respect to GND Terminal Voltage Temperature Under Bias Storage Temperature DC Output	with Respect to GND-0.5 to VccTerminal Voltage-0.5 to VccTemperature Under Bias-55 to +125Storage Temperature-65 to +150DC Output50

#### NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may

- cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to  $\leq$  20mA for the period of VTERM  $\geq$  Vcc + 10%.

### Capacitance

 $(TA = +25^{\circ}C, f = 1.0MHz)$  TQFP Only

Symbol	Parameter	Conditions	Мах.	Unit			
Cin	Input Capacitance	VIN = 3dV	8	pF			
Соит	Output Capacitance	Vout = 3dV	9	pF			
NOTEO							

#### NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from OV to 3V or from 3V to OV.

#### **Commercial Temperature Range**

# Maximum Operating Temperature and Supply Voltage<sup>(1,2)</sup>

Grade	Ambient Temperature		Vcc	
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%	
			3490 tbl 02	

#### NOTES:

1. This is the parameter TA. This is the "instant on" case temperature

2. Industrial temperature: for specific speeds, packages and powers contact your

### Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit			
Vcc	Supply Voltage	4.5	5.0	5.5	V			
GND	Ground	0	0	0	V			
V⊮	Input High Voltage	2.2	_	6.0 <sup>(2)</sup>	V			
Vil	Input Low Voltage	-0.5 <sup>(1)</sup>		0.8	V			
3490 tbl (								

NOTES:

1. VIL  $\geq$  -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			70914S		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current <sup>(1)</sup>	Vcc = 5.5V, VIN = 0V to Vcc	_	10	μA
Ilo	Output Leakage Current	$\overline{CE}$ = VIH, VOUT = 0V to VCC	_	10	μA
Vol	Output Low Voltage	Iol = +4mA	_	0.4	V
Vон	Output High Voltage	Ioh = -4mA	2.4	1	V

NOTE:

1. At Vcc < 2.0V, input leakages are undefined

#### 70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

**Commercial Temperature Range** 

3490 tbl 06b

## DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(4)</sup> ( $Vcc = 5V \pm 10\%$ )

				70914S12 Com'l Only		70914S15 Com'l Only		
Symbol	Parameter	Test Condition	Version	Typ. <sup>(2)</sup>	Max.	Тур. <sup>(2)</sup>	Max.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	$\label{eq:cell} \overline{CE}L \text{ and } \overline{CE}R = VIL, \\ Outputs \text{ Disabled} \\ f = f_{MAX}^{(1)}$	COM'L	190	310	180	300	mA
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_{L}$ and $\overline{CE}_{R} = V_{IH}$ f = fmax <sup>(1)</sup>	COM'L	95	150	90	140	mA
ISB2	Standby Current (One Port - TTL Level Inputs)	$  \frac{\overline{CE}^* A^* = VIL \text{ and } }{\overline{CE}^* B^* = VIH^{(3)} }                                  $	COM'L	170	220	160	210	mA
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	$\begin{array}{l} \hline Both \mbox{ Ports } \overline{\mbox{ CE}}_R \mbox{ and } \\ \hline \overline{\mbox{ CE}}_L \geq V \mbox{ Cc } & 0.2 V \\ \hline V \mbox{ V} \geq V \mbox{ cc } & 0.2 V \mbox{ or } \\ \hline V \mbox{ V} \leq 0.2 V,  f = 0^{(2)} \end{array}$	COM'L	10	15	10	15	mA
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\begin{array}{l} \overline{\underline{CE}}^{*} \mathbb{A}^{*} \leq 0.2 V \text{ and} \\ \overline{CE}^{*} \mathbb{B}^{*} \geq V \mathbb{CC} - 0.2 V^{(3)} \\ \forall \mathbb{N} \geq V \mathbb{CC} - 0.2 V \text{ or} \\ \forall \mathbb{N} \leq 0.2 V, \text{ Active Port} \\ Outputs Disabled \\ f = f_{MAX}^{(1)} \end{array}$	COM'L	165	210	155	200	mA

						3490 tbl 06a
				70914S20 Com'l Only		
Symbol	Parameter	Test Condition	Version	Typ. <sup>(2)</sup>	Max.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	$\label{eq:cell} \overline{CE}L \text{ and } \overline{CE}R = VIL, \\ Outputs \ Disabled \\ f = fMAx^{(1)}$	COM'L	170	290	mA
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CE}_{L}$ and $\overline{CE}_{R} = V_{IH}$ f = fMAX <sup>(1)</sup>	COM'L	85	130	mA
ISB2	Standby Current (One Port - TTL Level Inputs)	$\label{eq:cellson} \begin{array}{ c c } \hline \overline{CE}^{*} A^{*} = V \text{IL and} \\ \hline \overline{CE}^{*} B^{*} = V \text{IH}^{(3)} \\ \hline Active Port Outputs \\ \hline Disabled, f=f MAX^{(1)} \end{array}$	COM'L	150	200	mA
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	$\begin{array}{l} \hline Both \ Ports \ \overline{CE}{\sf R} \ and \\ \hline \overline{CE}{\sf L} \geq V{\sf Cc} \ - \ 0.2V \\ V{\scriptstyle  N} \geq V{\sf Cc} \ - \ 0.2V \ or \\ V{\scriptstyle  N} \leq 0.2V, \ f = 0^{(2)} \end{array}$	COM'L	10	15	mA
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\begin{array}{l} \overline{CE}^* A^* &\leq 0.2V \text{ and} \\ \overline{CE}^* B^* &\geq V \text{Cc} - 0.2V^{(3)} \\ V \text{IN} &\geq V \text{Cc} - 0.2V \text{ or} \\ V \text{IN} &\leq 0.2V, \text{ Active Port} \\ Outputs Disabled \\ f &= f \text{MAX}^{(1)} \end{array}$	COM'L	145	190	mA

NOTES:

1. At fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Vcc = 5V,  $Ta = 25^{\circ}C$  for Typ, and are not production tested. Icc bc = 150mA (Typ)

5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

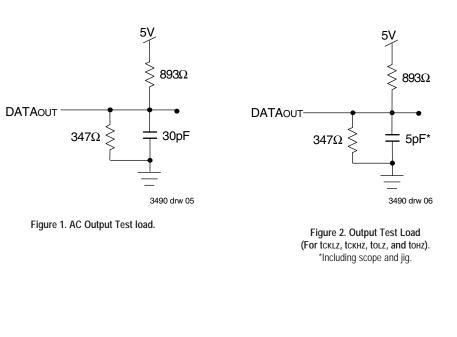
5

#### 70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

### AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

3490 tbl 07



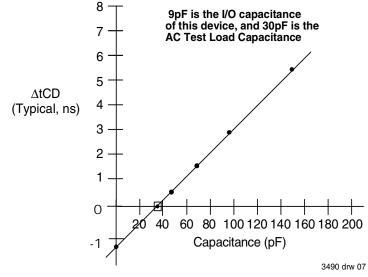


Figure 3. Typical Output Derating (Lumped Capacitive Load).

**Commercial Temperature Range** 

#### 70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

# AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)<sup>(3)</sup>

(Commercial:  $V_{CC} = 5V \pm 10\%$ , TA = 0°C to +70°C)

		70914S12 Com'l Only		70914S15 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
tcyc	Clock Cycle Time	16	-	20		ns
tсн	Clock High Time	6		6		ns
tcL	Clock Low Time	6		6	—	ns
tcD	Clock High to Output Valid		12		15	ns
ts	Registered Signal Set-up Time	4		4		ns
tн	Registered Signal Hold Time	1		1	—	ns
tDC	Data Output Hold After Clock High	3	_	3		ns
<b>t</b> CKLZ	Clock High to Output Low-Z <sup>(1,2)</sup>	2		2		ns
tскнz	Clock High to Output High-Z <sup>(1,2)</sup>		7		7	ns
toe	Output Enable to Output Valid		7		8	ns
toLz	Output Enable to Output Low-Z <sup>(1,2)</sup>	0	_	0		ns
tонz	Output Disable to Output High-Z <sup>(1,2)</sup>		7		7	ns
tscк	Clock Enable, Disable Set-up Time	4		4		ns
thck	Clock Enable, Disable Hold Time	2		2		ns
Port-to-Port	Delay					
tcwdd	Write Port Clock High to Read Data Delay		25		30	ns
tcss	Clock-to-Clock Setup Time		13		15	ns

3490 tbl 08a

			70914S20 Com'l Only		
Symbol	Parameter	Min.	Max.	Unit	
tcyc	Clock Cycle Time	20	_	ns	
tсн	Clock High Time	8		ns	
tc∟	Clock Low Time	8		ns	
tcd	Clock High to Output Valid		20	ns	
ts	Registered Signal Set-up Time	5		ns	
tн	Registered Signal Hold Time	1		ns	
tDC	Data Output Hold After Clock High	3	_	ns	
<b>t</b> CKLZ	Clock High to Output Low-Z <sup>(1,2)</sup>	2	_	ns	
tскнz	Clock High to Output High-Z <sup>(1,2)</sup>		9	ns	
toe	Output Enable to Output Valid		10	ns	
tolz	Output Enable to Output Low-Z <sup>(1,2)</sup>	0		ns	
tонz	Output Disable to Output High-Z <sup>(1,2)</sup>		9	ns	
tscк	Clock Enable, Disable Set-up Time	5		ns	
tнск	Clock Enable, Disable Hold Time	2		ns	
Port-to-Port	Delay		-	-	
tcwdd	Write Port Clock High to Read Data Delay		35	ns	
tcss	Clock-to-Clock Setup Time		15	ns	

3490 tbl 08b

#### NOTES:

1. Transition is measured 0mV from Low or High impedance voltage with the Output Test Load (Figure 2).

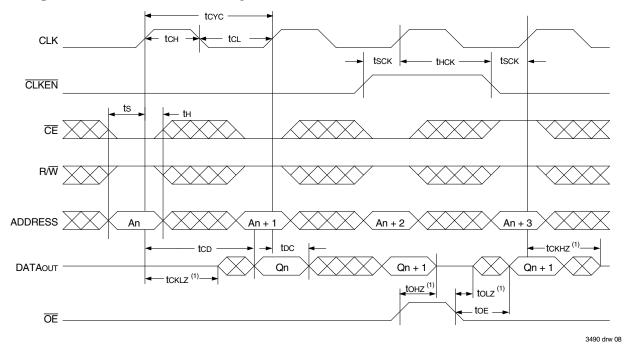
2. This parameter is guaranteed by device characterization, but is not production tested.

3. Industrial temperature: for specific speeds, packages and powers contact your sales office.

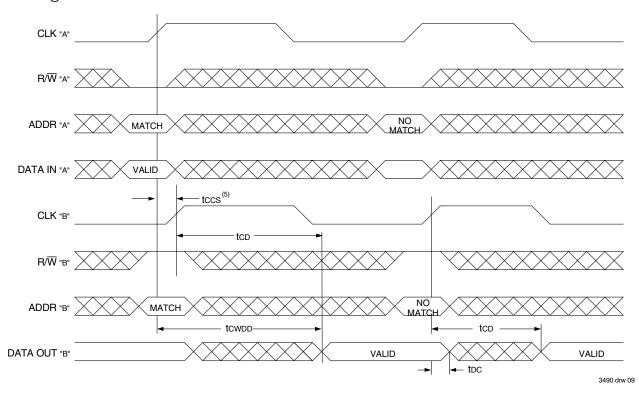
#### 70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

**Commercial Temperature Range** 

Timing Waveform of Read Cycle, Either Side



Timing Waveform of Write with Port-to-Port Read<sup>(2,3,4)</sup>

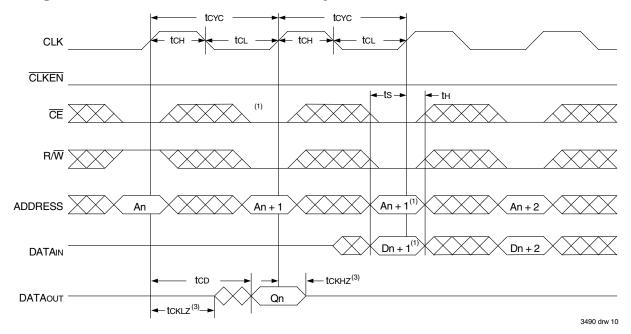


- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2.  $\overline{CE}_{L} = \overline{CE}_{R} = VIL, \overline{CLKEN}_{L} = \overline{CLKEN}_{R} = VIL.$
- 3.  $\overline{OE} = V_{IL}$  for the reading port, port 'B'.
- 4. All timing is the same for left and right ports. Ports "A" may be either the left or right port. Port "B" is opposite from port "A".
- 5. If tccs  $\leq$  maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb. tcwbb does not apply in this case.

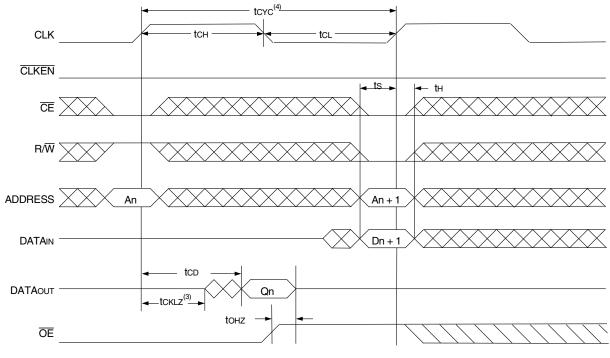
#### 70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

**Commercial Temperature Range** 

Timing Waveform of Read-to-Write Cycle No.  $1^{(1,2)}$  (tcyc = min.)



Timing Waveform of Read-to-Write Cycle No.  $2^{(4)}$  (tcyc > min.)



3490 drw 11

- For tcyc = min.; data out coincident with the rising edge of the subsequent write clock can occur. To ensure writing to the correct address location, the write must be repeated on the second write clock rising edge. If CE = VIL, invalid data will be written into array. The An+1 must be rewritten on the following cycle.
  OE LOW throughout.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. For tcyc > min.; OE may be used to avoid data out coincident with the rising edge of the subsequent write clock. Use of OE will eliminate the need for the write to be repeated.

### High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

### **Commercial Temperature Range**

### **Functional Description**

The IDT70914 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide very short set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal. An asynchronous output enable is provided to ease asynchronous bus interfacing.

The internal write pulse width is dependent on the LOW to HIGH

transitions of the clock signal allowing the shortest possible realized cycle times. Clock enable inputs are provided to stall the operation of the address and data input registers without introducing clock skew for very fast interleaved memory applications.

A HIGH on the  $\overline{CE}$  input for one clock cycle will power down the internal circuitry to reduce static power consumption.

# Truth Table I: Read/Write Control<sup>(1)</sup>

Inputs		Outputs				
Sy	nchronou	s <sup>(3)</sup>	Asynchronous	-		
CLK			I/O0-8	Mode		
$\uparrow$	Н	Х	Х	High-Z	Deselected, Power-Down	
$\uparrow$	L	L	Х	DATAIN	Selected and Write Enabled	
$\uparrow$	L	Н	L	DATAOUT	Read Selected and Data Output Enable Read	
$\uparrow$	Х	Х	Н	High-Z	Outputs Disabled	

3490 tbl 09

### Truth Table II: Clock Enable Function Table<sup>(1)</sup>

	Inputs		Register Inputs		Register Outputs <sup>(4)</sup>			
Mode	CLK <sup>(3)</sup>	CLKEN <sup>(2)</sup>	ADDR	DATAIN	ADDR	DATAOUT		
Load "1"	Ŷ	L	Н	Н	Н	Н		
Load "0"	Ŷ	L	L	L	L	L		
Hold (do nothing)	↑	Н	Х	Х	NC	NC		
	Х	Н	Х	Х	NC	NC		
3490 tbl 10								

NOTES:

1. 'H' = HIGH voltage level steady state, 'h' = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'L' = LOW voltage level steady state 'l' = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'X' = Don't care, 'NC' = No change

2. CLKEN = VIL must be clocked in during Power-Up.

3. Control signals are initiated and terminated on the rising edge of the CLK, depending on their input level. When R/W and CE are LOW, a write cycle is initiated on the LOW-to-HIGH transition of the CLK. Termination of a write cycle is done on the next LOW-to-HIGH transition of the CLK.

4. The register outputs are internal signals from the register inputs being clocked in or disabled by CLKEN.

70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM Commercial Temperature F											
Ordering Information											
XXXXX	A	99	A	A	Α	A					
Device Type	Power	Speed	Package		Process/ Temperature Range		Blank 8	Tray Tape and Reel			
							Blank I <sup>(1)</sup>	Commercial (0°C to +70°C) Industrial (-40°C to +85°C)			
							G	Green			
							PF	80-pin TQFP (PNG80)			
							12	Commercial Only } Speed in nanoseconds			
							S	Standard Power			
							70914	36K (4K x 9-Bit) Synchronous Dual-Port RAM			

3490 drw 12

#### NOTES:

 Industrial temperature range is available on selected TQFP packages in standard power. For specific speeds, packages and powers contact your sales office. LEAD FINISH (SnPb) parts are Obsoleted. Product Discontinuation Notice - PDN# SP-17-02 Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

### Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
12	70914S12PFG	PNG80	TQFP	С
	70914S12PFG8	PNG80	TQFP	С

### 70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

Commercial Temperature Range

# Datasheet Document History

	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Page 2 and 3 Added additional notes to pin configurations
	Changed drawing format
	Replaced IDT logo
Page 4	Increased storage temperature parameter
0	Clarified TA parameter
Page 5	DC Electrical parameters-changed wording from "open" to "disabled"
5	Changed ±200mV to 0mV in notes
	Removed PGA pinout (obsolete package)
	Changed cycle time of 12ns part from 17ns (58MHz) to 16ns (60MHz)
Page 11	Removed "IDT" from orderable part number
Page 1	Added green parts availability to features
Page 11	Added green indicator to ordering information
	Removed Military and Industrial Temperature Ranges from datasheet header
-	Removed Military speed offerings from the Features
	Removed MIL-PRF 38535 QML support information
•	The package codes J68-1 and PN80-1 changed to J68 and PN80
	Removed the military and industrial offerings in the Absolute Max Ratings & the Max Operating Temp tables
	Removed the military and industrial offerings in the DC Elec Chars tables
	Corrected typo in the Typical Output Derating drawing
Page 7	Removed military offering for the 20 & 25 speed grades in the AC Elec Chars table
	Removed the military temp range information from the AC Elec Chars table title
Page 11	Added Tape and Reel to and removed military offering & 25ns speed grade from the Ordering Information
Page 2	Changed diagram for the J68 pin configuration by rotating package pin labels and pin numbers 90 degrees
	clockwise to reflect pin1 orientation and added pin 1 dot at pin 1
	Removed all four chamfers from J68 and aligned the top and bottom pin labels in the standard direction
Page 3	Changed diagram for the PN80 pin configuration by rotating package pin labels and pin numbers 90 degrees
	counter clockwise to reflect pin 1 orientation and added pin 1 dot at pin 1
	Added the IDT logo, changed the text to be in alignment with new diagram marking specs
	for all pin configurations and updated footnote references for the J68 & the PN80 pin configurations
Page 11	Removed Industrial temp range information from the Ordering Information
	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
Page 1 & 11	Deleted obsolete Commercial speed grades 15/20ns
Page 1 & 11	Deleted obsolete PLG68 PLCC package
Page 11	Added Orderable Part Information table
	Page 1 Page 11 Pages 1-12 Page 2 Pages 2,3 &11 Page 4 Page 5 Page 6 Page 7 Page 11 Page 2 Page 3 Page 11 Page 1 & 11 Page 1 & 11

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